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Docket No. 99600-1DIV

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REMARKS

Claims 3-25 are all the claims presently pending in the application. Claims 3, 4, 6, 17, 18 and 22 have been amended to more particularly define the invention.

It is noted that the claim amendments are made only for more particularly pointing out the invention, and not for distinguishing the invention over the prior art, narrowing the claims or for any statutory requirements of patentability. Further, Applicant specifically states that no amendment to any claim herein should be construed as a disclaimer of any interest in or right to an equivalent of any element or feature of the amended claim.

Applicant gratefully acknowledges the Examiner's indication that claims 8-12 and 15-16 are allowed. However, applicant respectfully submits that all of the claims are allowable.

Applicant notes that the claims are not subject to any prior art rejections and therefore, presumably would be allowable if the alleged informalities are addressed.

Claims 3-7, 13-14 and 18-21 and 23-25 stand rejected under 35 U.S.C. § 112, first paragraph. Claims 4 and 17-22 stand rejected under 35 U.S.C. § 112, second paragraph.

These rejections are respectfully traversed in the following discussion.

II. THE 35 USC 112, FIRST PARAGRAPH REJECTION

The Examiner alleges that 3-7, 13-14 and 18-21 and 23-25 contain subject matter that was not described in the specification in such a way as to reasonably convey to one of ordinary skill in the art that the inventor had possession of the claimed invention. Applicant submits, however, that the claimed invention was clearly and completely described in the specification.

Specifically, Applicant notes that claim 3 has been amended to delete the phrase *"implanting n-type impurities within an NMOSFET forming region during a formation of channel regions and n-type source/drain regions"*.

Further, claim 6 has been amended to recite *"the acceleration energy of the phosphorous ion is not greater than 10 [[15]] keV"*.

Further, with respect to claim 13, Applicant would point out that the feature recited in claim 13 (*"wherein point defects generated by said implanting phosphorous ions are absorbed by said amorphous silicon, such that diffusion of said phosphorous ions during said*

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heat-treating is suppressed") is discussed in the specification at least at page 11, lines 6-10.

Further, Applicant would point out that to satisfy the written description requirement, a patent specification need only describe the claimed invention in sufficient detail that one skilled in the art can reasonably conclude that the inventor had possession of the claimed invention (e.g., *Moba, B.V. v. Diamond Automation, Inc.*, 325 F.3d 1306, 1319, 66 USPQ2d 1429, 1438 (Fed. Cir. 2003); *Vas-Cath, Inc. v. Mahurkar*, 935 F.2d at 1563, 19 USPQ2d at 1116). Further, Applicant may show possession of the claimed invention by describing the claimed invention with all of its limitations using such descriptive means as words, structures, figures, diagrams, and formulas that fully set forth the claimed invention. *Lockwood v. American Airlines, Inc.*, 107 F.3d 1565, 1572, 41 USPQ2d 1961, 1966 (Fed. Cir. 1997).

In this case, Applicant submits that the specification (e.g., at page 14, lines 5-12) clearly describes the claimed invention (e.g., as recited in claim 13) in sufficient detail that one skilled in the art can reasonably conclude that the inventor had possession of the claimed invention of claim 13.

Therefore, Applicant submits that the claimed invention was clearly and completely described in the specification. Therefore, the Examiner is respectfully requested to withdraw this rejection.

III. THE 35 USC 112, SECOND PARAGRAPH REJECTION

The Examiner alleges that claims 4 and 17-22 are indefinite as failing to particularly point out and distinctly claim the subject matter regarded as the invention. Applicant submits, however, that the claims are clearly defined and not indefinite.

Specifically, Applicant notes that claim 4 has been amended to recite "further comprising: implanting wherein n-type impurities are implanted in the NMOSFET region to form an n-type extension region before said implanting said two different ions".

Claim 17 has been amended to recite "wherein where an arsenic concentration of said n-type source/drain main region is between $1 \times 10^{20}/\text{cm}^3$ [$[\text{cm}^2]$] and $5 \times 10^{21}/\text{cm}^3$ [$[\text{cm}^2]$] and a phosphorous concentration in said n-type source/drain buffer region is between $1 \times 10^{18}/\text{cm}^3$ [$[\text{cm}^2]$] and $5 \times 10^{19}/\text{cm}^3$ [$[\text{cm}^2]$]".

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Claim 18 has been amended to recite "further comprising: wherein implanting said boron ions are implanted in said semiconductor substrate to form a well region, said arsenic ions being implanted in said well region of said semiconductor substrate".

Further, claim 22 has been amended to recite "using a same photoresist mask as a photoresist mask used in said implanting said second arsenic ions, implanting phosphorous ions in said arsenic ion implanted regions at an acceleration energy level which is no greater than 10 keV for implanting said second arsenic ions, so as to form a concentration peak of the phosphorous ions located in the arsenic ion implanted regions region".

Therefore, Applicant submits the claims are clearly defined and not indefinite. Therefore, the Examiner is respectfully requested to withdraw this rejection.

IV. FORMAL MATTERS AND CONCLUSION


In view of the foregoing, Applicant submits that claims 3-25, all the claims presently pending in the application, are patentably distinct over the prior art of record and are in condition for allowance. The Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Should the Examiner find the application to be other than in condition for allowance, the Examiner is requested to contact the undersigned at the local telephone number listed below to discuss any other changes deemed necessary in a telephonic or personal interview.

The Commissioner is hereby authorized to charge any deficiency in fees or to credit any overpayment in fees to Attorney's Deposit Account No. 50-0481.

Date: 6/23/06

Respectfully Submitted,



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